CLAIMS

[1] A cleaning agent composition for a substrate for a semiconductor device, the cleaning agent composition containing a component A, a component B, a component C, and a component D,

the component A being sulfuric acid;

the component B being ascorbic acid;

the component C being at least one of thiourea and dithiothreitol; and

the component D being water,

wherein a mass ratio B/C of a content of the component B to a content of the component C is 0.13 to 8 inclusive,

wherein a total content of the component B and the component C at the time of cleaning is 0.006 mass% to 0.045 mass% inclusive, and

wherein a content of the component A at the time of cleaning is 0.01 mass% to 0.3 mass% inclusive.

[2] The cleaning agent composition according to claim1, further containing

a dispersing agent (a component E).

[3] A method for cleaning a substrate for a semiconductor device, the method comprising

a cleaning step of cleaning a substrate to be cleaned, using the cleaning agent composition according to claim 1 or 2,

wherein the substrate to be cleaned is a substrate that has processed polishing using a polishing liquid composition containing ceria.

[4] A method for manufacturing a substrate for a semiconductor device, the method comprising

a cleaning step of cleaning a substrate to be cleaned, using the cleaning agent composition according to claim 1 or 2,

wherein the substrate to be cleaned is a substrate that has processed polishing using a polishing liquid composition containing ceria.